WR0596 ṂṂㄴ ∧ȍỠᄇ͠ ǁ ᄀ

Ultrafast Recovery Diode in a TO-263 Plastic Package.

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Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

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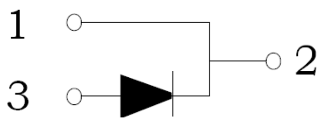
For high frequency, high voltage, high current rectifier diode, freewheeling diode.



PIN1 χ Anode PIN 2 4 χ Cathode PIN 3 χ Anode

ȸ м ˥ ب ˝ See Marking Instructions

v῍Ω Parameter	ɬ ᴺ Symbol	῍ΩӪ Rating	ᴅ ɧ Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Maximum Average Forward Current	I_F	1 × 30	A
Peak forward surge current	I_{FSM}	300	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.0	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v῍Ω Parameter	ɬ ᴺ Symbol	╜ ꜝ ͳ Test Conditions	ῳ ŋ Ӫ Min	Ɛ ʒ Ӫ Typ	ῳ ᶻ Ӫ Max	ᴅ ɧ Unit
Forward Voltage	V_F	I_F=5.0A T_C=25			1.35	V
		I_F=5.0A T_C=150			1.15	
		I_F=30A T_C=25			1.65	
		I_F=30A T_C=150			1.25	
Instantaneous Reverse Current [Note1]	I_R	V_R=600V T_a=25			0.25	mA
		V_R=420V T_a=150			1	
		V_R=600V T_a=150			2	
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{RR}=0.25A			50	ns

├2Notes

1. Ǽ ͳ ǁ ˜ ￼╜ ꜝ ʽH ڗ ıΦ ő ˛ᵒᵒ Ṉ₅ ♬ ῴ Ẕ 2Short duration pulse test used to minimize self-heating effect.

2. ڻ ̊ ⁼ ├ ˝ ı ῍ΩӪ ҈ A ϶ ɑ￼v῍Ω 2 Unless otherwise noted, values for the parameters of a single chip

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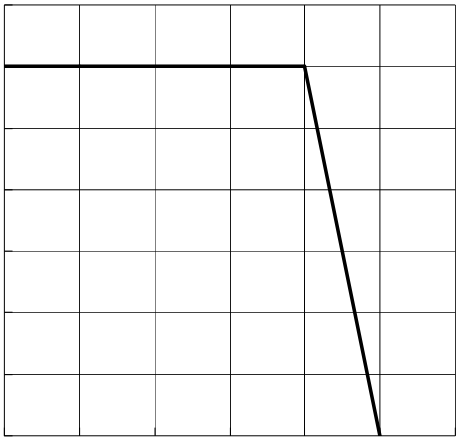
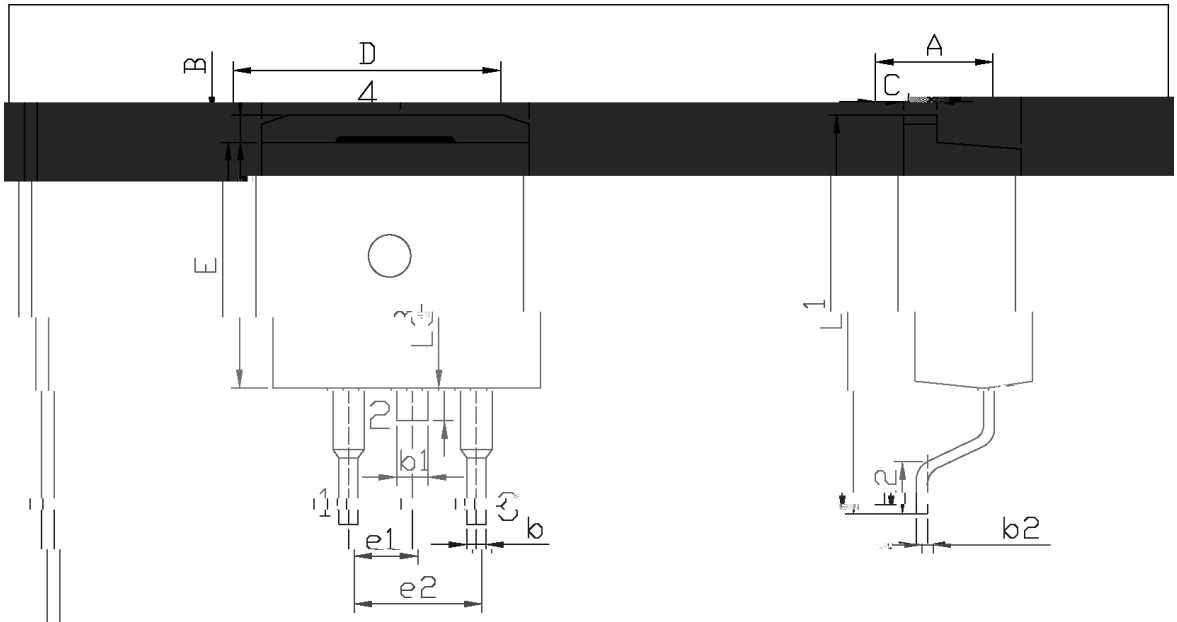
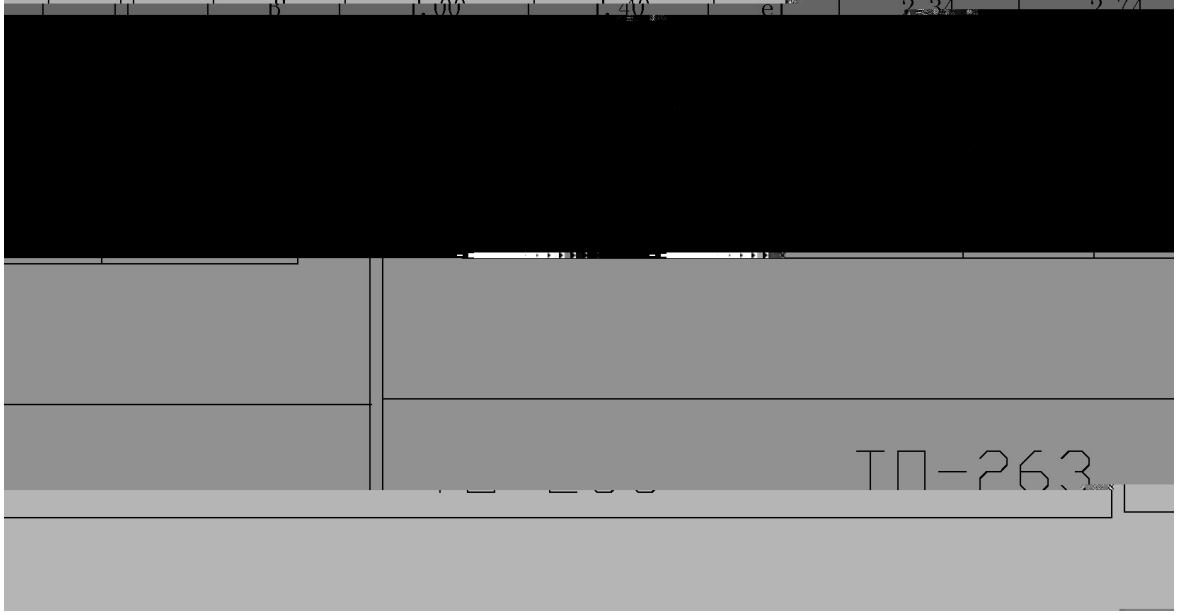
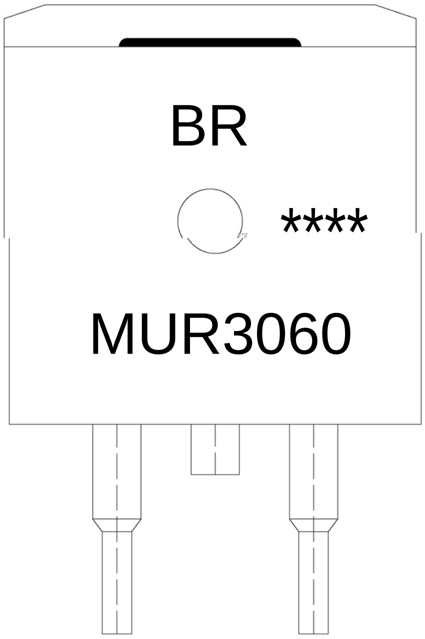




单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeter	
	Min	Max		Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.34	2.74





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EU χ	ꞛ ʇ ᴻ ꞁƀ
P XU6393 χ	ꞛ ғ ᵝ ʒ ᴺ
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Note:	
BR:	Company Code
MUR3060 χ	Product Type.
****:	Lot No. Code, code change with Lot No.